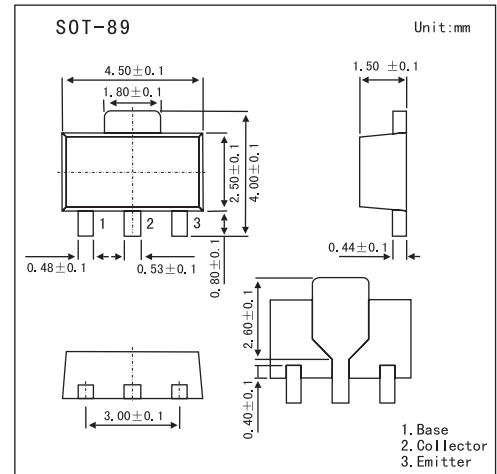


Epitaxial Planar PNP Transistor

KTA1661

■ Features

- High Voltage: $V_{CEO}=-120V$
- High Transition Frequency: $f_T=120MHz$
- Small Flat Package

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ C$

* mounted on ceramic substrate (250mm²X0.8t)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=-120V, I_E=0$			-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{CE}=5V, I_C=0$			-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-120			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5.0			V
DC Current Gain	h_{FE}	$V_{CE}=-5V, I_C=-100mA$	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5V, I_C=-500mA$			-1.0	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-100mA$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			30	pF

■ hFE Classification

Marking	DO	DY
Rank	O	Y
Type	80~160	120~240